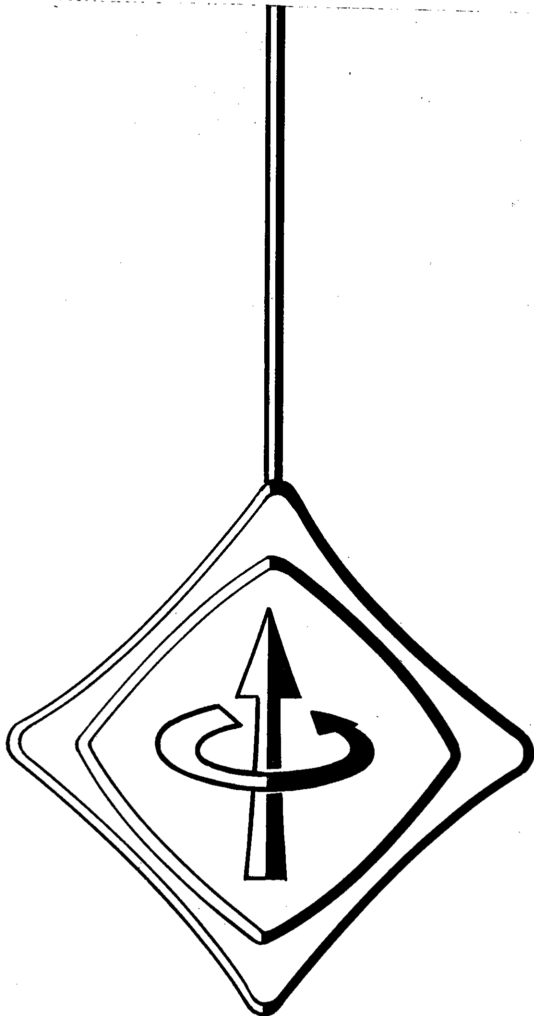

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RELIABILITY PHYSICS AWARD PRESENTATION

Joseph Vaccaro, award recipient (at left)
David F. Barber, general chairman of the Symposium (at right)

The IEEE Reliability Physics Symposium Award for Outstanding Contributions to the field of Reliability Physics was authorized by vote of the Symposium Board of Directors. This award, which is not necessarily given annually, is to be presented to individuals who, by their work, have made major significant contributions to the advancement of the field of reliability.

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TABLE OF CONTENTS

KEYNOTE ADDRESS—Gen. Spencer F. Hunn, FAA

"Reliability in The Federal Aviation Administration" 1

METALLIZATION AND BONDING

Chairman and Organizer: Arnie Lesk

INTERMETALLIC CHARACTERIZATION
L. Zakraysek 6

DISSOLUTION RATES AND RELIABILITY EFFECTS OF Au, Ag, Ni, AND Cu IN LEAD BASE SOLDERS
H. M. Berg and E. L. Hall 10

BONDING DEGRADATION IN THE TANTALUM NITRIDE—CHROMIUM—GOLD METALLIZATION SYSTEM
N. T. Panousis and H. Bonham 21

TO-5 DISCOLORATION AND BONDABILITY
G. Riga 26

ON MEASURING THE MECHANICAL PROPERTIES OF ALUMINUM METALLIZATION AND THEIR RELATIONSHIP TO RELIABILITY PROBLEMS
E. M. Philofsky and K. V. Ravi 33

A BONDING—WIRE FAILURE MODE IN PLASTIC—ENCAPSULATED INTEGRATED CIRCUITS
C. Adams 41

HYBRID CIRCUITS AND PASSIVE COMPONENTS

Chairman and Organizer: Jake Martin

THE SOLID TANTALUM CAPACITOR—A "SOLID" CONTRIBUTOR TO RELIABILITY
B. J. Mandakis 45

AN ELUSIVE OPEN CIRCUIT FAILURE MODE IN THIN FILM CHIP RESISTORS
A. H. Cronshagen and R. S. Spriggs 54

FURTHER STUDIES ON THE RELIABILITY OF THIN—FILM NICKEL—CHROMIUM RESISTORS
W. M. Paulson 61

COMPONENT LINEARITY TEST IMPROVES RELIABILITY SCREENING THROUGH MEASUREMENT OF THIRD HARMONIC INDEX
A. Salomon and A. E. Troianello 69

TORQUE AND THERMAL CYCLING AS METHODS OF TESTING RELIABILITY OF REFLOW—SOLDERED CHIP TO SUBSTRATE JOINTS
M. L. Ailawadhi and A. K. Kakar 77

WIRE—BOND RELIABILITY IN HYBRID MICROCIRCUITS
R. S. Spriggs and A. H. Cronshagen 83

RELIABILITY OF CONDUCTORS AND CROSSOVERS FOR FILM INTEGRATED CIRCUITS
D. P. Brady and A. Pfahnl 89

ALMOST ALL YOU WERE AFRAID TO ASK AND HEAR ABOUT HYBRID CIRCUIT RELIABILITY

Co-Organizers: Jayne Partridge and Jake Martin

SOME RELIABILITY CONSIDERATIONS OF LARGE HYBRIDS
R. E. McMahon 91

IBM RELIABILITY EXPERIENCE WITH HYBRID MICROCIRCUITS
P. A. Totta 92

RELIABILITY OF SOLDER–CONNECTED, THICK–FILM HYBRID INTEGRATED CIRCUITS
D. P. Burkes 93

W. D. McKee 93

ENGINEERING RELIABILITY
G. Waite 94

FAILURE ANALYSIS WORKSHOP

Organizer and Moderator: Al Tamburrino

PACKAGE HERMETICITY
G. E. Adams 95

FAILURE ANALYSIS OF WIRE BONDS
H. A. Schafft 98

ANALYSIS OF ELECTRICAL–OVERSTRESS FAILURES
J. S. Smith 105

FAILURE ANALYSIS OF OXIDE DEFECTS
G. H. Ebel and H. A. Engelke 108

FAILURE ANALYSIS OF SURFACE INVERSION
W. Schroen 117

FAILURE ANALYSIS

Chairman and Organizer: Harold Nigh

USE OF A PULSE LASER TECHNIQUE IN FAILURE ANALYSIS
W. E. Reese 124

MOS/LSI FAILURE ANALYSIS TECHNIQUES
G. Gear 127

ANALYSIS OF INTEGRATED CIRCUIT FAILURE MODES AND FAILURE MECHANISMS DERIVED FROM HIGH TEMPERATURE OPERATING LIFE TESTS
R. A. Vetter 133

NONCONTACT TESTING OF INTERCONNECTIONS IN FILM INTEGRATED CIRCUITS USING AN ELECTRON BEAM
J. M. Sebeson, D. K. Hindermann, and W. L. Harrod 138

TEMPERATURE–HUMIDITY ACCELERATION OF METAL–ELECTROLYSIS FAILURE IN SEMICONDUCTOR DEVICES
D. S. Peck and C. H. Zierdt, Jr. 146

MOS INTERFACE PROPERTIES

Chairman and Organizer: Don Kerr

TEMPERATURE BIAS AGING OF (HCl) MOS STRUCTURES
R. J. Kriegler and T. F. Devenyi 153

IMPROVED V_T STABILITY OF SNOS FET'S BY OXYGEN ANNEALING
R. C. Dockerty, C. A. Barile, A. Nagarajan and S. M. Zalar 159

AVALANCHE BREAKDOWN IN POLYCRYSTALLINE SILICON FILMS
C. A. Neugebauer, J. F. Burgess, R. E. Joynson, and J. L. Mundy 163

ROOM TEMPERATURE THRESHOLD–VOLTAGE INSTABILITIES IN AN MOS INTEGRATED CIRCUIT
F. H. Reynolds 170

EFFECTS OF MECHANICAL STRESS ON THE ELECTRICAL BEHAVIOR OF MOS DEVICE STRUCTURES
B. C. Wonsciewicz and D. V. McCaughan 177

WORKSHOP ON FAILURE ANALYSIS USING THE SCANNING ELECTRON MICROSCOPE, ELECTRON MICROPROBE, AUGER SPECTROMETER, AND ION MICROPROBE

Organizers and Conductors: John Colby and Tony Gonzales

FAILURE ANALYSIS APPLICATIONS OF THE SCANNING ELECTRON MICROSCOPE
A. J. Gonzales 179

FAILURE ANALYSIS APPLICATIONS OF AUGER ELECTRON SPECTROSCOPY
A. J. Gonzales 185

FAILURE ANALYSIS USING THE ELECTRON MICROPROBE
J. W. Colby 189

FAILURE ANALYSIS USING THE ION MICROPROBE
J. W. Colby 194

DESIGN AND PROCESS CONTROL FOR RELIABILITY

Chairman and Organizer: George Schnable

ELECTROSTATIC GATE PROTECTION USING AN ARC GAP DEVICE
L. W. Linholm and R. F. Plachy 198

A PROCESS CONTROL TEST FOR LATERAL CHARGE SPREADING SUSCEPTIBILITY
G. A. Brown, K. Lovelace, and C. Hutchins 203

RELIABILITY IMPROVEMENTS IN ELECTRON BOMBARDED SEMICONDUCTOR POWER DEVICES
D. J. Bates, A. Silzars and A. Ballonoff 208

IMPROVED RELIABILITY OF ELECTRONIC DEVICES THROUGH OPTIMIZED COVERAGE OF SURFACE TOPOGRAPHY
W. Kern, J. L. Vossen, and G. L. Schnable 214

RELIABILITY IMPROVEMENTS OF PLASTIC SEMICONDUCTORS USING GOLD METALLIZATION
J. Wright 224

WHO WANTS RELIABLE PLASTIC SEMICONDUCTORS?
E. B. Hakim, G. Malinowski, and R. Holevinski 230

HIGH–RELIABILITY PLASTIC PACKAGE FOR INTEGRATED CIRCUITS
H. Khajezadeh 236

A CURRENT–PULSE SCREENING TEST FOR METAL STEP COVERAGE
H. S. Gurev 245

SCREENING OF METALLIZATION STEP COVERAGE ON INTEGRATED CIRCUITS
D. L. Crosthwait, Jr., P. B. Ghate, and D. M. Smith 254

MICROWAVE AND OPTOELECTRONIC DEVICES

Chairman and Organizer: George Schneer

DEGRADATION OF III–V COMPOUND LED'S WITH PLASTIC LENSES
H. Okamoto, S. Nakaya, and Y. Arai 261

DEGRADATION STUDIES OF DIFFUSED GaAs ELECTROLUMINESCENT DIODES SUBJECTED TO MECHANICAL STRESS
W. A. Brantley and D. A. Harrison 267

DYNAMIC THERMAL PROPERTIES OF IMPATT DIODES
T. J. Rossiter 275

FABRICATION TECHNIQUES AND SCREENING PROCEDURES FOR HIGH RELIABILITY TRANSFERRED ELECTRON DIODES
T. E. Walsh 282

MEDIAN TIME TO FAILURE (MTF) OF MICROWAVE POWER TRANSISTORS UNDER RF CONDITIONS
W. E. Poole 287

PULSED RF LIFE OF AN L–BAND POWER TRANSISTOR
K. H. Fischer 293

FAILURE MODEL FOR ELECTROMIGRATION
R. A. Sigsbee 301